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D25XB80

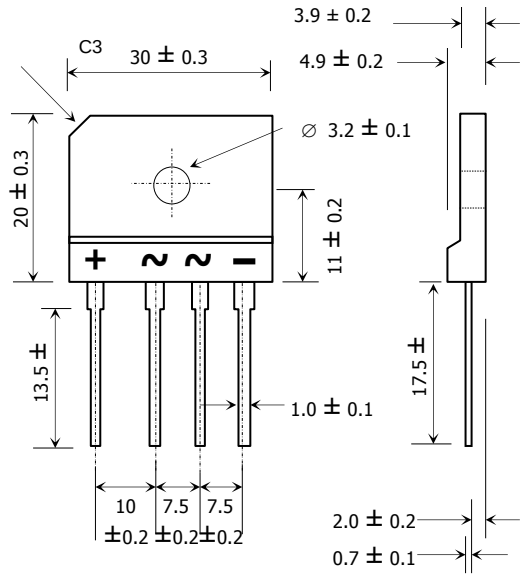
SILICON BRIDGE RECTIFIERS

PRV : 800 Volts
Io : 25 Amperes

FEATURES :
* High current capability
* High surge current capability
* High reliability
* Low reverse current
* Low forward voltage drop
* Ideal for printed circuit board
* Very good heat dissipation
* Pb / RoHS Free

MECHANICAL DATA :
* Case : Reliable low cost construction utilizing molded plastic technique
* Epoxy : UL94V-O rate flame retardant
* Terminals : Plated lead solderable per MIL-STD-202, Method 208 guaranteed
* Polarity : Polarity symbols marked on case
* Mounting position : Any

RBV25



Dimensions in millimeters

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS
Rating at 25 °C ambient temperature unless otherwise specified.
Single phase, half wave, 60 Hz, resistive or inductive load.
For capacitive load, derate current by 20%.

RATING	SYMBOL	VALUE	UNIT
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	800	V
Maximum RMS Voltage	V_{RMS}	560	V
Maximum DC Blocking Voltage	V_{DC}	800	V
Maximum Average Forward Current 60 Hz sine wave, R-load	$I_{F(AV)}$	25 (With heatsink, Tc = 87°C) 3.5 (Without heatsink, Ta = 25°C)	A
Peak Forward Surge Current, 60Hz sine wave Non-repetitive 1 cycle peak value, Tj = 25 °C	I_{FSM}	320	A
Current Squared Time at t < 8.3 ms.	I^2t	424	A^2S
Maximum Forward Voltage per Diode at I_F = 12.5 A	V_F	1.0	V
Maximum DC Reverse Current Ta = 25 °C at Rated DC Blocking Voltage	I_R	5	µA
Operating Junction Temperature Range	T_J	- 55 to + 150	°C
Storage Temperature Range	T_{STG}	- 55 to + 150	°C

RATING AND CHARACTERISTIC CURVES (D25XB80)

FIG.1 - DERATING CURVE FOR OUTPUT RECTIFIED CURRENT

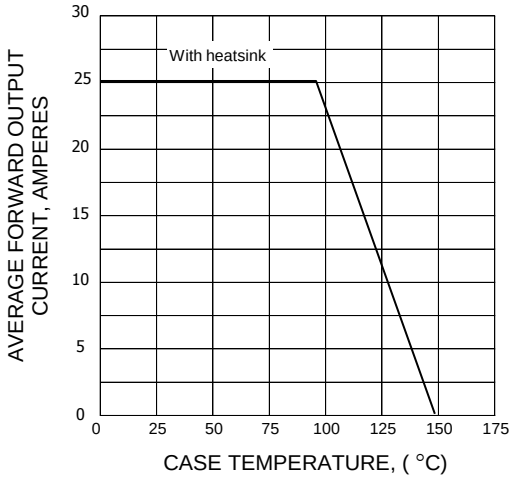


FIG.2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

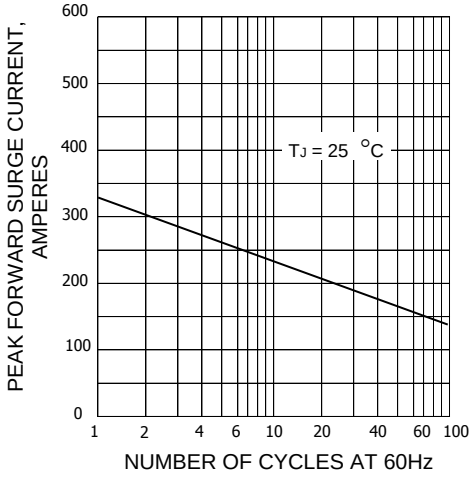


FIG.3 - TYPICAL FORWARD CHARACTERISTICS PER DIODE

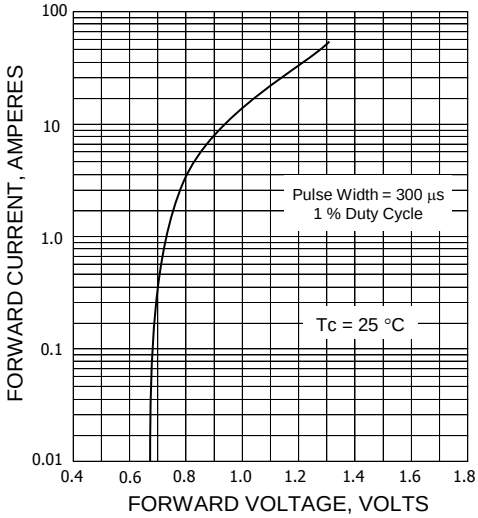


FIG.4 - TYPICAL REVERSE CHARACTERISTICS PER DIODE